

Average gate power dissipation ($T_j=125$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	4	kV

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33\Omega$	- -	MAX.	10	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k\Omega$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	25	mA
				30	
I_H	$I_T=500mA$		MAX.	15	mA
dV/dt	$V_D=400V$ Gate Open $T_j=125$		MIN.	500	V/ μs
$(dI/dt)_c$	$(dV/dt)_c=10V/\mu s$ $T_j=125$		MIN.	5	A/ms
t_{on}	$I_G=20mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25$		TYP.	5	μs
t_{off}				30	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=22.5A$ $t_p=380\mu s$	$T_j=25$	1.5	V
V_{TO}	Threshold voltage	$T_j=125$	0.77	V
R_D	Dynamic resistance	$T_j=125$	30	$m\Omega$
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25$	5	μA
I_{RRM}		$T_j=125$	0.4	mA

ORDERING INFORMATION

J	ST	16	A	-600	SW
JieJie Microelectronics Co., Ltd.	Triacs	$I_T(RMS):16A$	A:TO-220A(Ins)	600: V_{DRM}/V_{RRM} 600V	SW:IGT1-3 10mA

MARKING

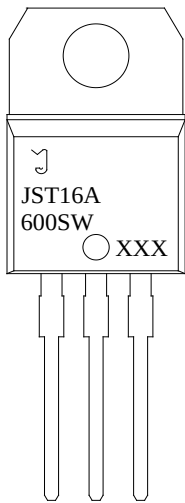
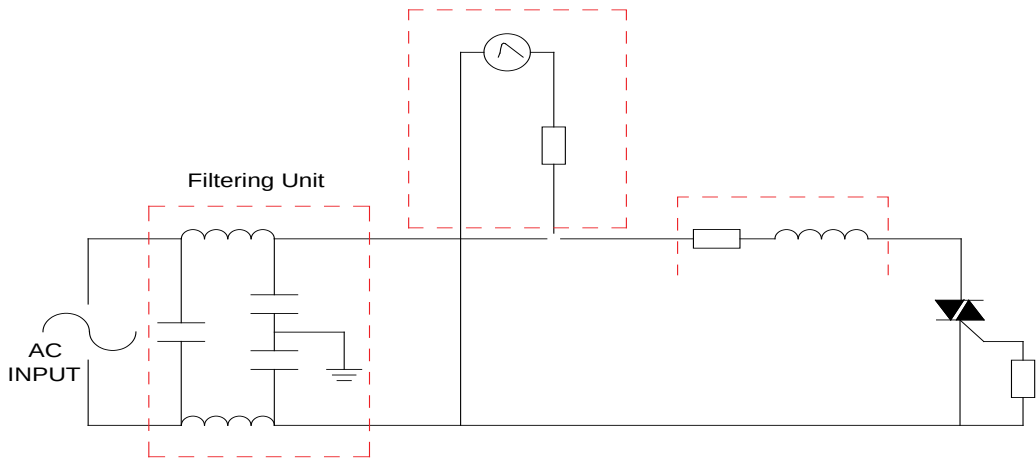


FIG.1: Maximum power dissipation versus RMS on-state current

FIG.2: RMS on-state current versus case temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards

I2-24.5999 2-2.1C



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